

LNN04R040-VB Datasheet

N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
40	0.0025 at $V_{GS} = 10$ V	120	38 nC
	0.0028 at $V_{GS} = 6.5$ V	105	

FEATURES

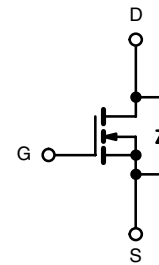
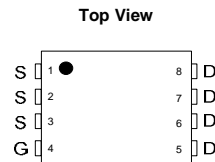
- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested



RoHS
COMPLIANT

APPLICATIONS

- Synchronous Rectification
- Secondary Side DC/DC



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	120	A
		80	
		33 ^{b, c}	
		26 ^{b, c}	
Pulsed Drain Current	I_{DM}	360	A
Continuous Source-Drain Diode Current	I_S	100	
		4.9 ^{b, c}	
Single Pulse Avalanche Current	I_{AS}	40	
Single Pulse Avalanche Energy	E_{AS}	80	mJ
Maximum Power Dissipation	P_D	83	W
		53	
		5.4 ^{b, c}	
		3.4 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	18	23	$^\circ\text{C/W}$
Maximum Junction-to-Case (Drain)	R_{thJC}	1.0	1.5	

Notes:

a. Based on $T_C = 25^\circ\text{C}$.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 10$ s.

d. Maximum under steady state conditions is 90°C/W .

e. Calculated based on maximum junction temperature. Package limitation current is 80 A.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	40			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		43		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 6		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V			1	μA
		V _{DS} = 40 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	100			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0025		Ω
		V _{GS} =6.5 V, I _D = 20 A		0.0028		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A		102		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz		4750		pF
Output Capacitance	C _{oss}			610		
Reverse Transfer Capacitance	C _{rss}			275		
Total Gate Charge	Q _g	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 20 A		78	117	nC
		V _{DS} = 20 V, V _{GS} = 4.5 V, I _D = 20 A		38	57	
Gate-Source Charge	Q _{gs}			13		
Gate-Drain Charge	Q _{gd}			11		
Gate Resistance	R _g	f = 1 MHz	0.2	0.7	1.4	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 20 V, R _L = 2 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		14	25	ns
Rise Time	t _r			9	18	
Turn-Off Delay Time	t _{d(off)}			41	65	
Fall Time	t _f			9	18	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 20 V, R _L = 2 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω		33	42	
Rise Time	t _r			22	35	
Turn-Off Delay Time	t _{d(off)}			42	65	
Fall Time	t _f			13	25	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C		50		A
Pulse Diode Forward Current ^a	I _{SM}			60		
Body Diode Voltage	V _{SD}	I _S = 5 A		0.75	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C		40	60	ns
Body Diode Reverse Recovery Charge	Q _{rr}			48	72	nC
Reverse Recovery Fall Time	t _a			24		ns
Reverse Recovery Rise Time	t _b			16		

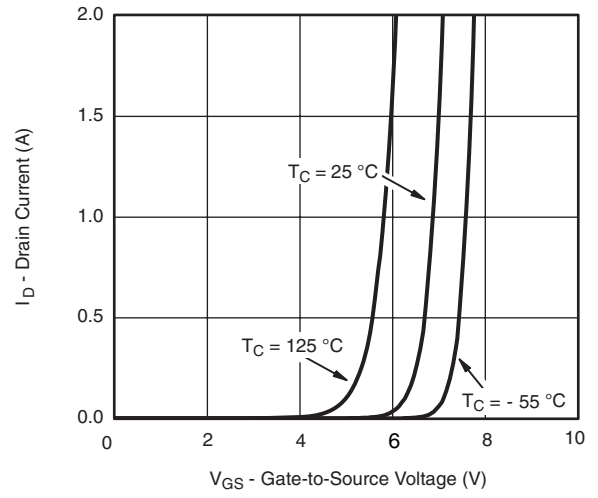
Notes:

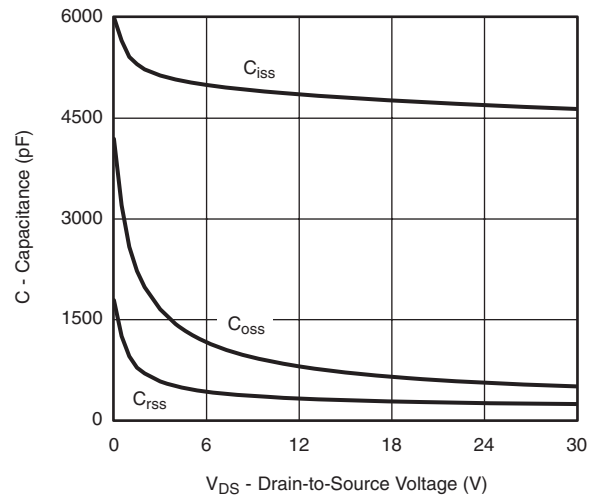
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

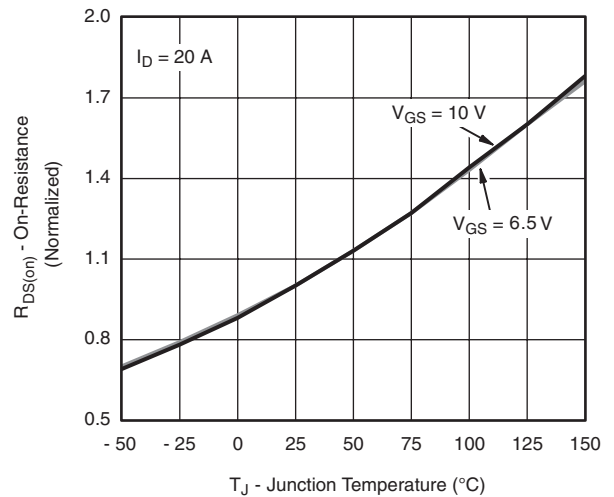
b. Guaranteed by design, not subject to production testing.

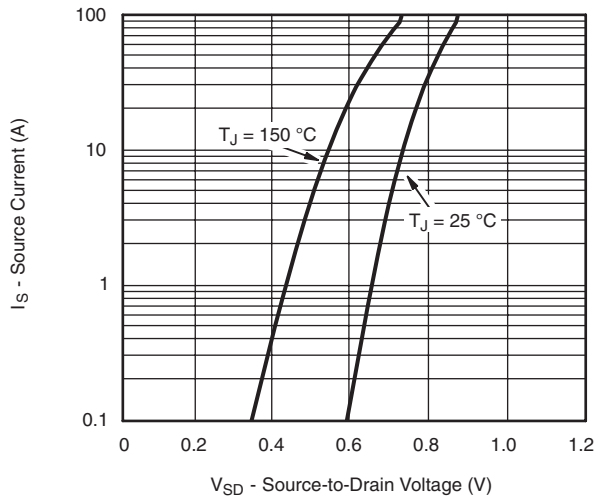
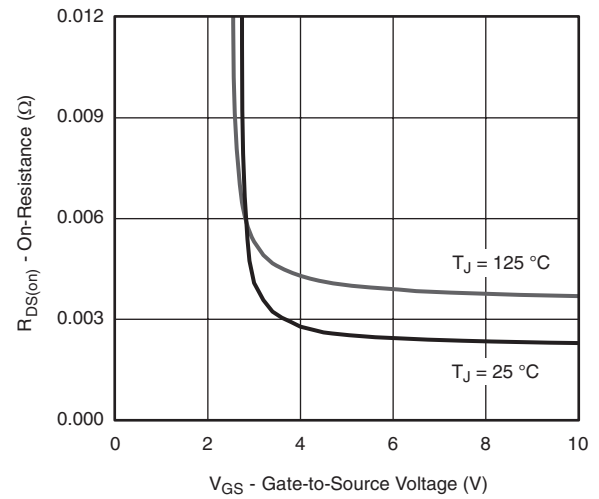
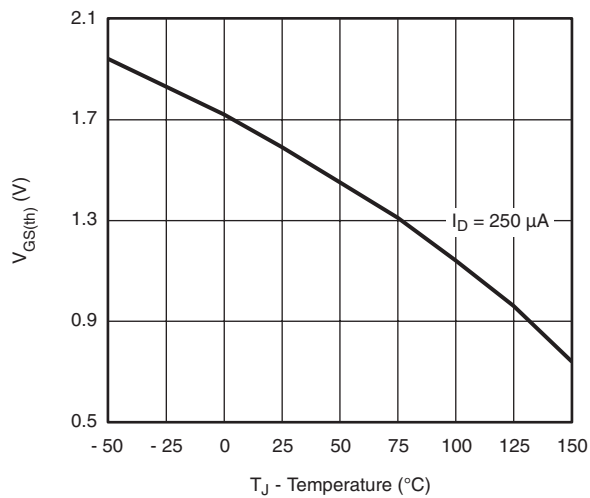
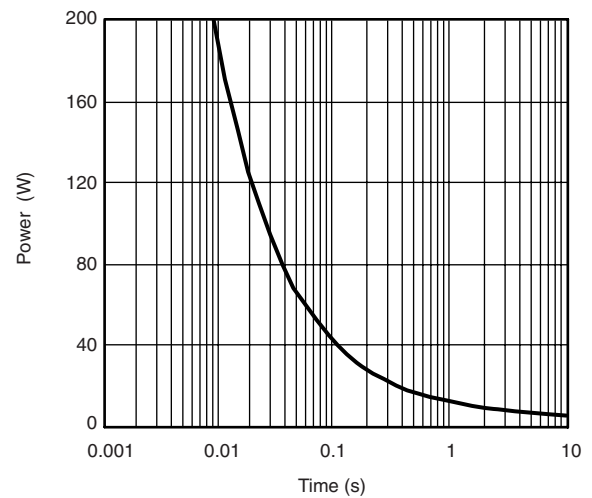
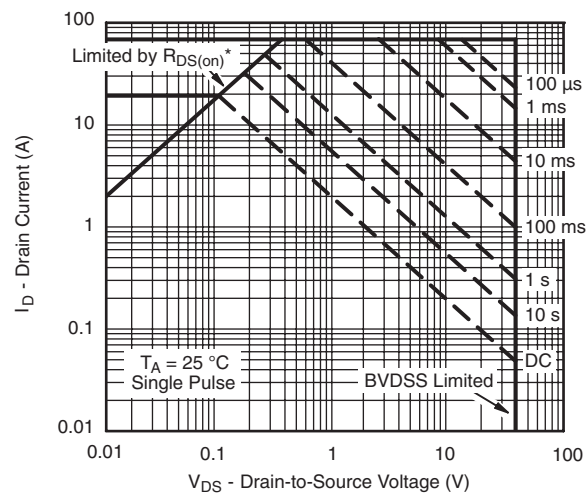
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

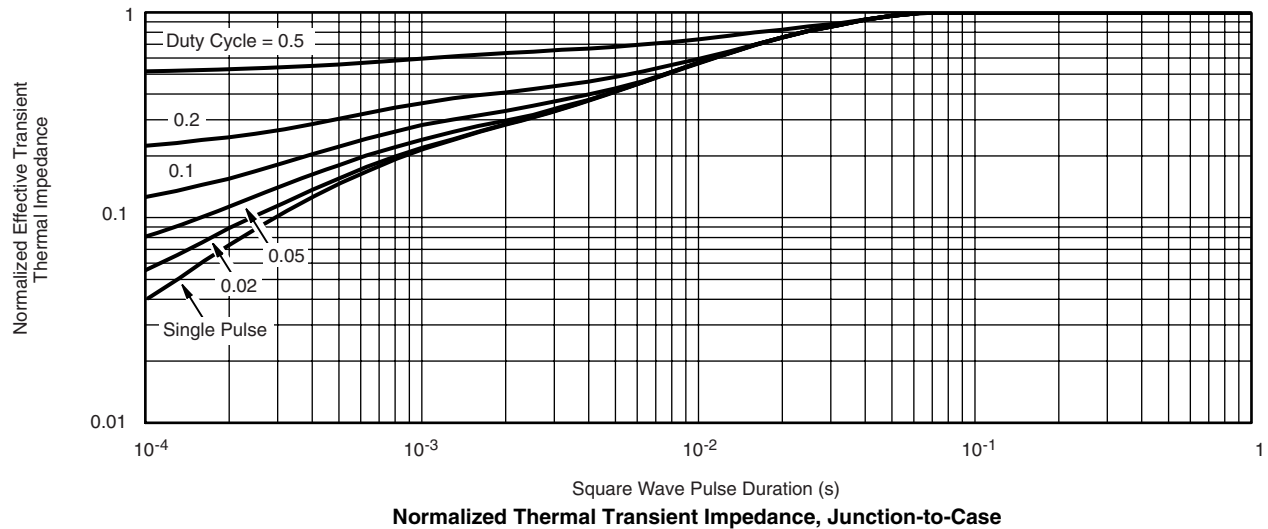
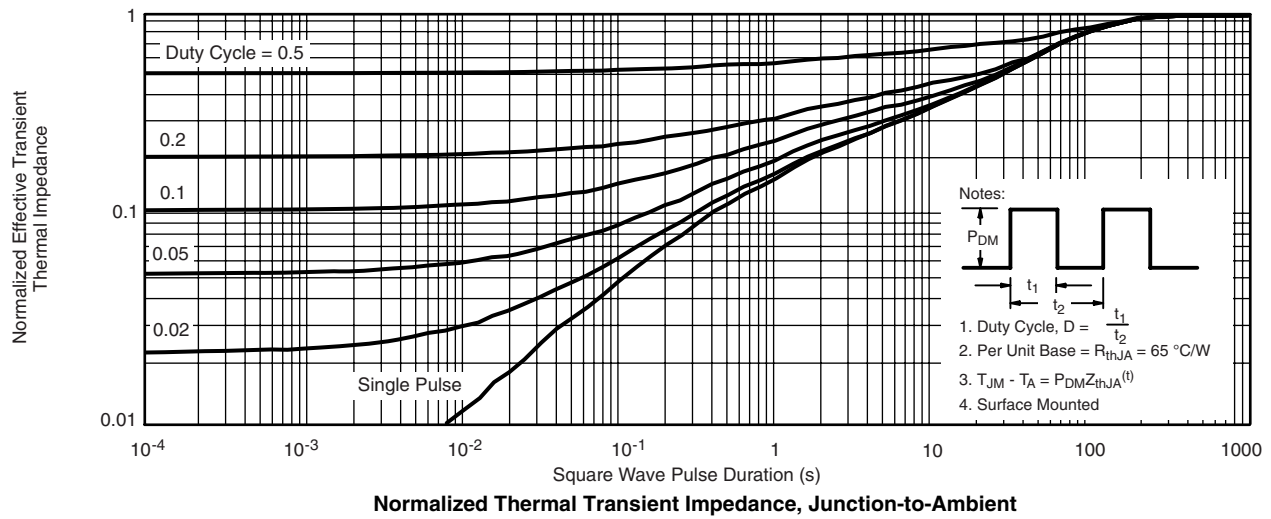
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

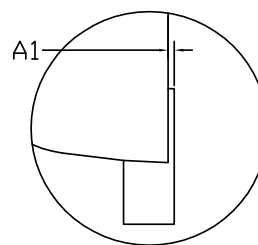
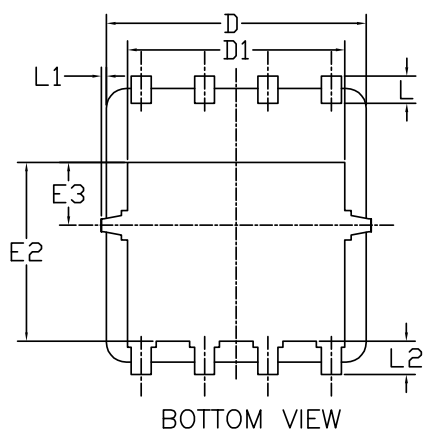
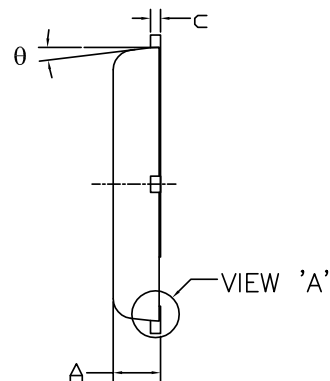
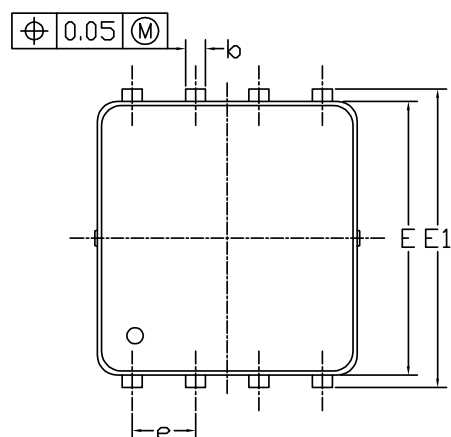
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

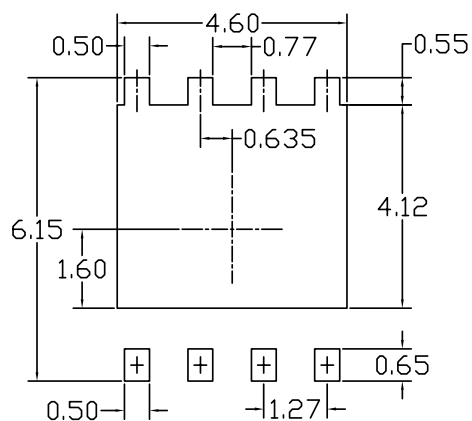

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


DFN5x6_8L_EP1_P PACKAGE OUTLIN


 VIEW 'A'
 (SCALE 5:1)

RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

NOTE

UNIT: mm

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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